

## KT9155V

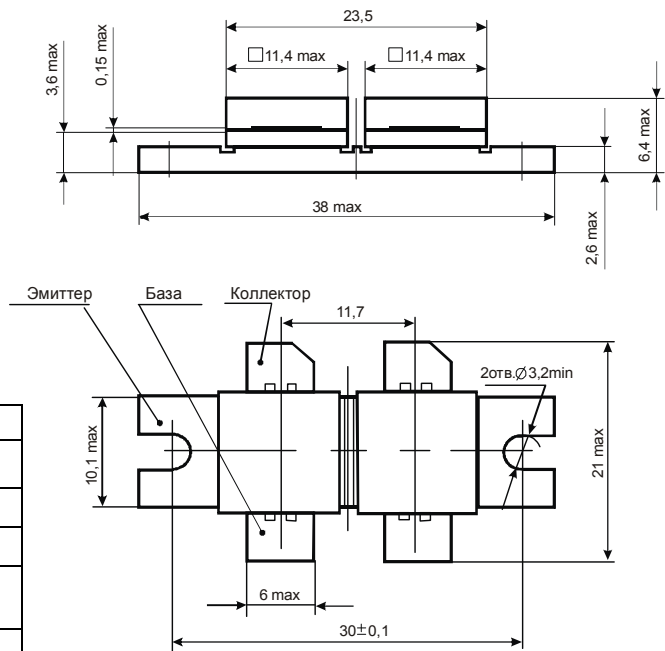
### NPN SILICON RF POWER TRANSISTOR

Designed for operation in Class AB linear push-pull power amplifiers of TV and radio transmitters

- Output power = 100 W,  $f = 860$  MHz,  $V_{CC} = 28$  V
- Power gain = 5 dB (min)
- Efficiency = 45% (min)

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CER}$	50	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	$I_C$	24	A
Operating Junction Temperature	$T_j$	+200	°C
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Thermal Resistance (junction to case)	$R_{\theta JC}$	0.75	°C/W
Total Power Dissipation, $T_C=25$ °C	$P_D$	233	W



Case KT-82

#### FUNCTIONAL TESTS

Characteristics	Symbol	Value			Unit
		min	typ	max	
Common-Emitter Amplifier Power Gain ( $V_{CC} = 28$ V, $P_{out} = 100$ W @ 1 dB Comp., $f = 860$ MHz)	$G_P$	5			dB
Collector Efficiency ( $V_{CC} = 28$ V, $P_{out} = 100$ W, $f = 860$ MHz)	$\eta_c$	45			%

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Specification is subject to change without notice